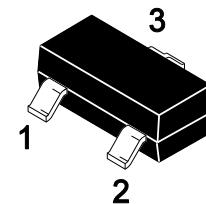




## Features

- Fast switching
- Low gate charge and  $R_{DS(ON)}$
- Low reverse transfer capacitances

SOT-23



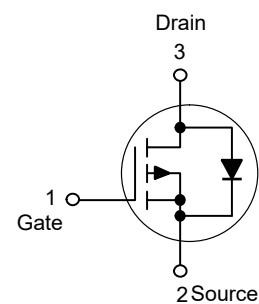
1. Gate 2. Source 3. Drain

**Marking: S5**

## Application

- Load switch and in PWM applications
- Power management

**Schematic Diagram**



## Absolute Maximum Ratings

Ratings at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

Parameter	Symbol	Value	Units
Drain-Source Voltage	$-V_{DS}$	12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current	$-I_D$	4.1	A
Power Dissipation	$P_D$	1.4	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	150, -55 to 150	$^\circ\text{C}$

## Thermal Characteristics

Parameter	Symbol	Typ.	Units
Maximum Junction-to-Ambient <sup>Note1</sup>	$R_{\theta JA}$	89	$^\circ\text{C}/\text{W}$



**Electrical Characteristics (T<sub>a</sub>=25°C unless otherwise specified)**

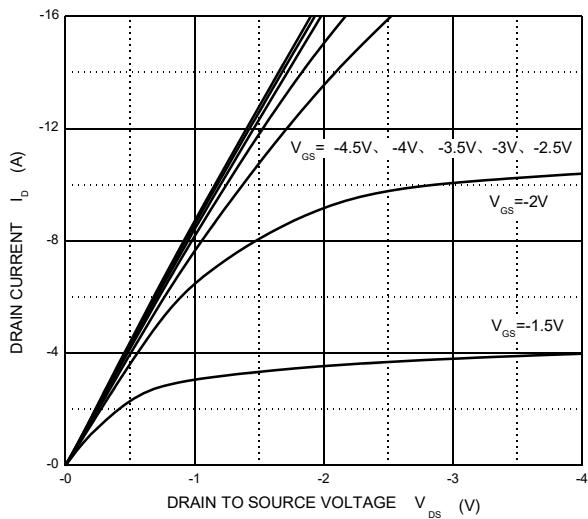
Parameter	Symbol	Test Condition	Min	Type	Max	Units
<b>Static Characteristics</b>						
Drain-source breakdown voltage	-V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	12			V
Drain to Source Leakage Current	-I <sub>DSS</sub>	V <sub>DS</sub> = -12V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage <sup>Note1</sup>	-V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	0.5		0.9	V
Drain-source on-resistance <sup>Note1</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A		45	60	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3A		55	70	mΩ
		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -2.0A		75	90	mΩ
Forward transconductance <sup>Note1</sup>	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.1A	6			S
<b>Dynamic characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -4V, V <sub>GS</sub> = 0V, f = 1MHz		740		pF
Output Capacitance	C <sub>oss</sub>			290		
Reverse Transfer Capacitance	C <sub>rss</sub>			190		
<b>Switching Characteristics</b>						
Turn-on delay time	t <sub>d(on)</sub>	I <sub>D</sub> = -3.3A, V <sub>DD</sub> = -4V, V <sub>GS</sub> = -4.5V, R <sub>GEN</sub> = 1Ω,		13		ns
Turn-on rise time	t <sub>r</sub>			35		
Turn-off delay time	t <sub>d(off)</sub>			32		
Turn-off fall time	t <sub>f</sub>			10		
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = -4V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.1A V <sub>DD</sub> = -4V, V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -4.1A		4.5	9	nC
Gate-source charge	Q <sub>gs</sub>			1.2		
Gate-drain charge	Q <sub>gd</sub>			1.6		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	-V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.3A			1.2	V
Continuous source-drain diode current	-I <sub>S</sub>				1.4	A

Note: 1. Pulse Test ; Pulse Width ≤300μs, Duty Cycle ≤2%.

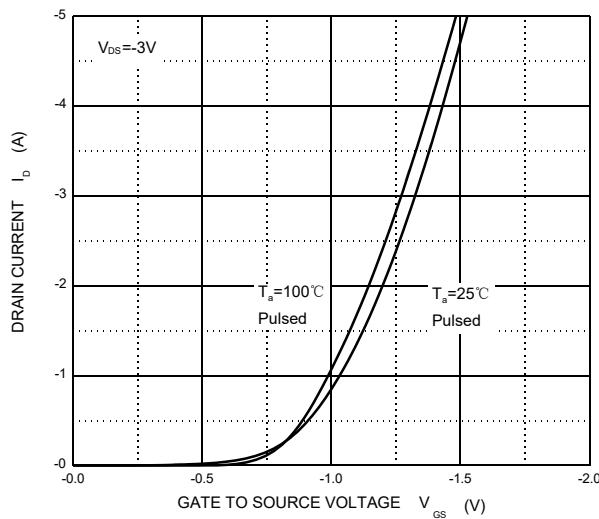


## Typical Characteristic Curves

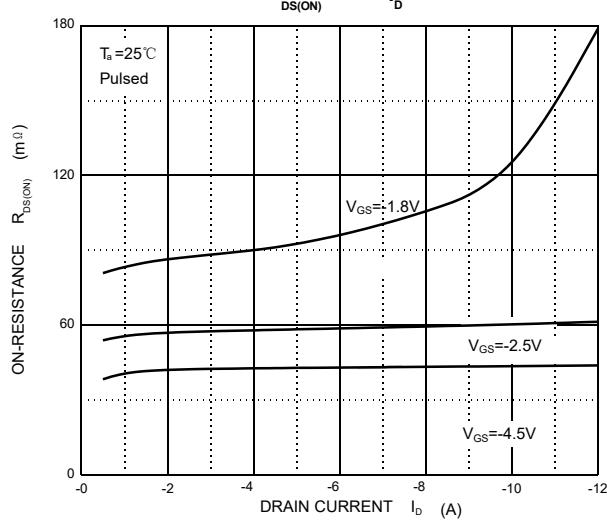
Output Characteristics



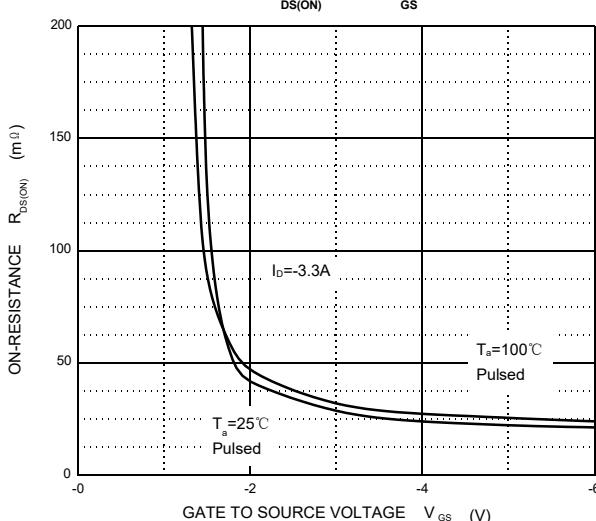
Transfer Characteristics



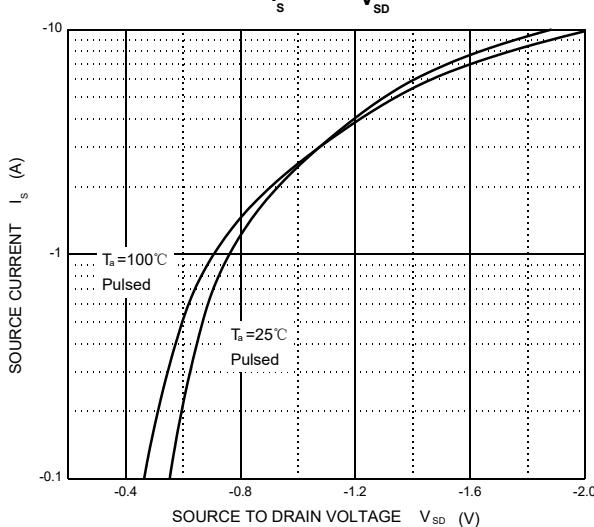
$R_{DS(ON)}$  —  $I_D$



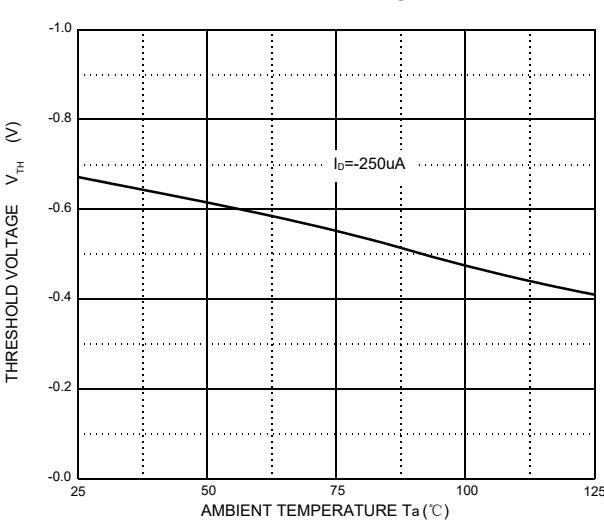
$R_{DS(ON)}$  —  $V_{GS}$

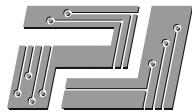


$I_s$  —  $V_{SD}$



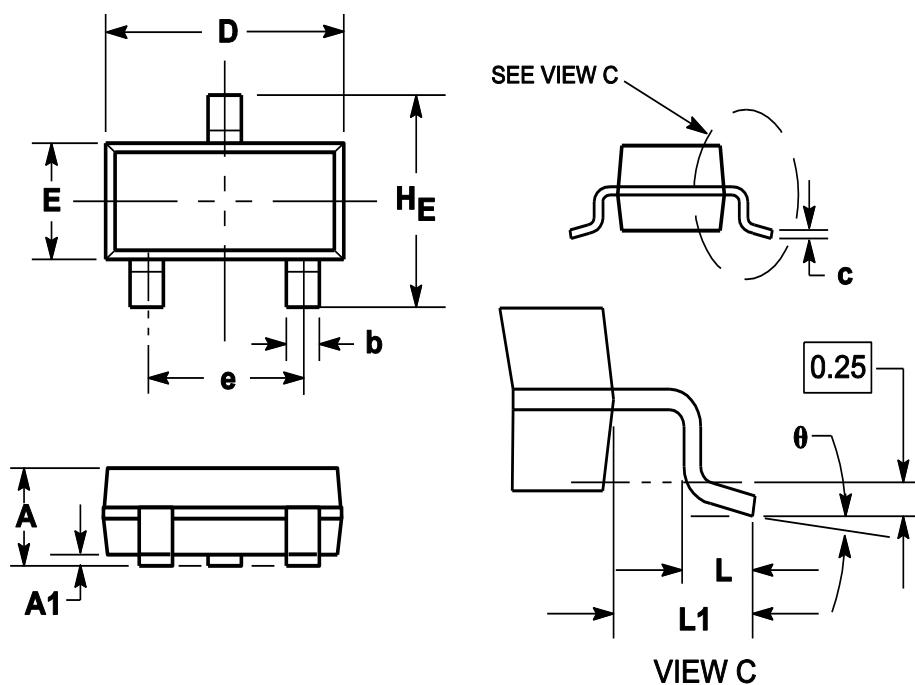
Threshold Voltage



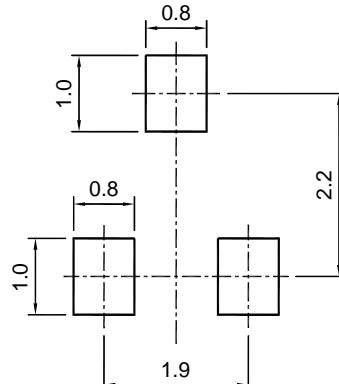


## Package Outline

SOT-23



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.050	0.100
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
HE	2.250	2.400	2.550
e	1.800	1.900	2.000
L1	0.550REF		
L	0.300		0.500
θ	0°		8°



SOT-23 (TO-236)

**Recommended soldering pad**

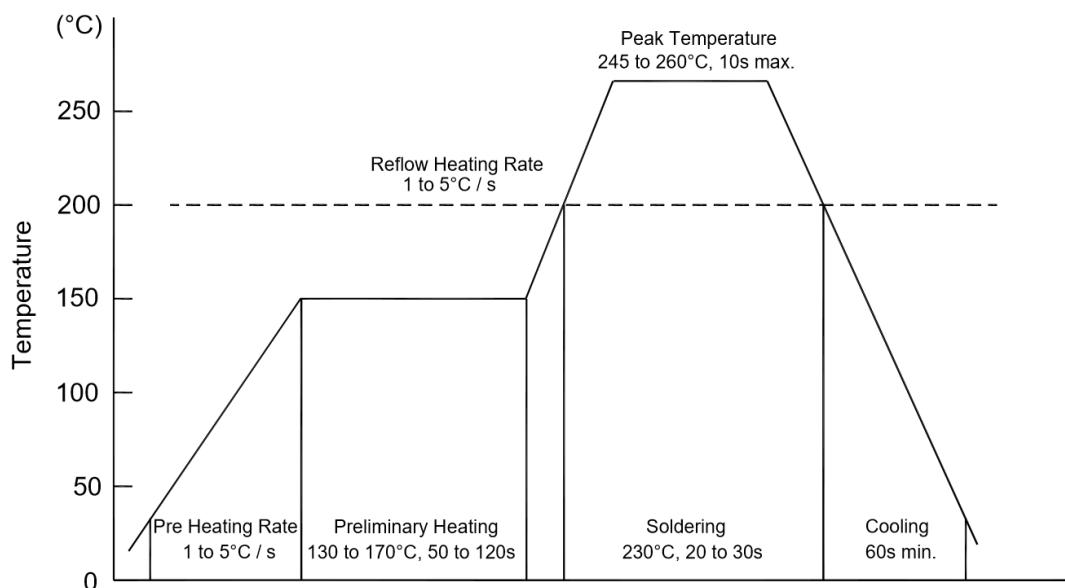
## Ordering Information

Device	Package	Shipping
PJM2305PSA	SOT-23	3000PCS/Reel&Tape



## Conditions of Soldering and Storage

### ◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

### ◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

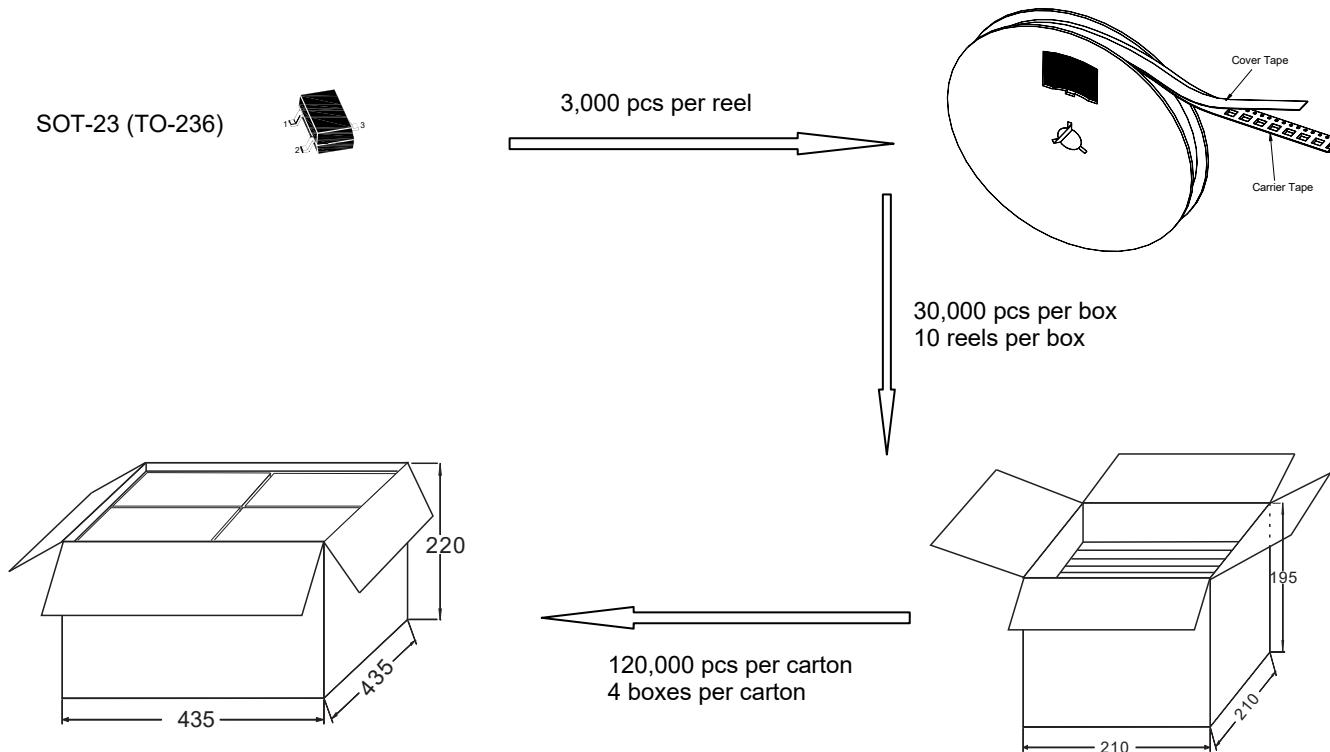
### ◆ Storage conditions

- **Temperature**  
5 to 40 °C
- **Humidity**  
30 to 80% RH
- **Recommended period**  
One year after manufacturing

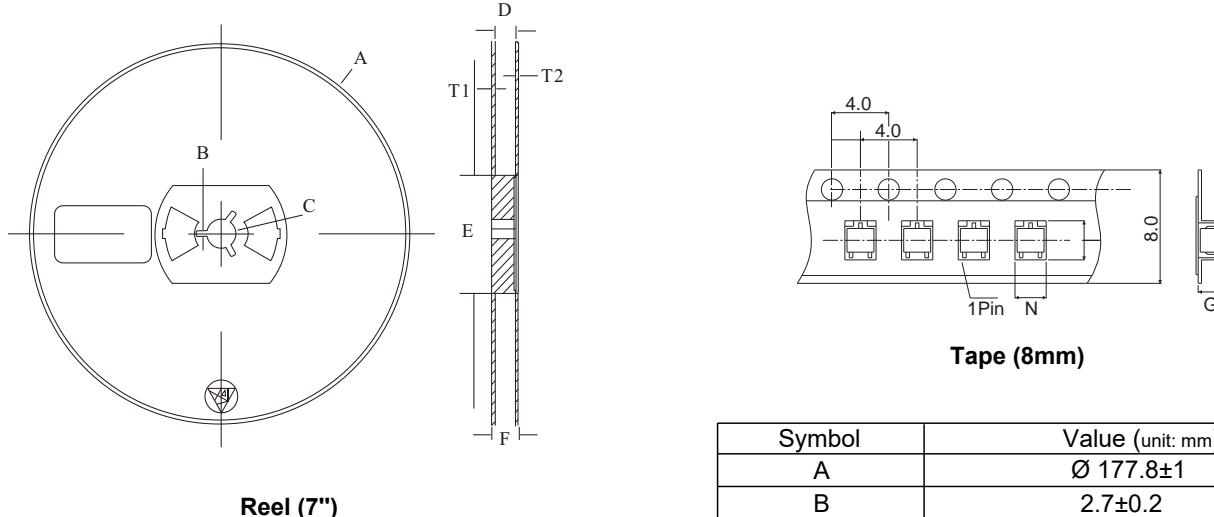


## Package Specifications

- The method of packaging



### ◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	$\varnothing 177.8 \pm 1$
B	$2.7 \pm 0.2$
C	$\varnothing 13.5 \pm 0.2$
E	$\varnothing 54.5 \pm 0.2$
F	$12.3 \pm 0.3$
D	$9.6 +2/-0.3$
T1	$1.0 \pm 0.2$
T2	$1.2 \pm 0.2$
N	$3.15 \pm 0.1$
G	$1.25 \pm 0.1$

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